



Crystal Properties			
PARAMETER	UNITS	SPECIFICATION	NOTE
Crystalline structure	-	Monocrystalline	
Growth technique	-	Czochralski (Cz)	
Orientation	-	<100>±1°	
Slice orientation	Degrees	ON±1.0°	
Electrical Properties			
PARAMETER	UNITS	SPECIFICATION	NOTE
Conductance type	-	P-type	
Dopant	-	Boron	
Resistivity	Ω-cm	10 – 20	
Geometrical Properties			
PARAMETER	UNITS	SPECIFICATION	NOTE
Diameter	mm	100±0.50	
Thickness	μm	525±25	
TTV	μm	≤5	
Warp	μm	≤30	
Bow	μm	≤30	
Flats	-	2 per SEMI Standard	
Primary flat length	mm	32.50±2.50	
Primary flat orientation	-	<110>±1°	
Secondary flat location		90°±5° from primary flat	
Secondary flat length	mm	18.00±2.00	
Surface Appearance			
PARAMETER	UNITS	SPECIFICATION	NOTE
Front surface	-	Polished	
Back surface	-	Etched	
Frontside particles ≥0.30 μm (LPD & COP)	No./wafer	≤20	
Nominal Edge Exclusion	mm	3.0	
Wafer Identification			
PARAMETER	UNITS	SPECIFICATION	NOTE
Lasermark	-	None	
Surface Metals			
APPLICABLE METALS	UNITS	SPECIFICATION	NOTE
Al, Ca, Cl, Cr, Cu, Fe, K, Na, Ni, Zn	Atoms/cm ₂	≤5E10	